

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) An apparatus for forming a thin film, comprising:
a reaction chamber having a top portion, a sidewall portion and a bottom portion;
a gas injector penetrating the top portion and letting a source element pass therethrough;
a thin film distributor, the thin film distributor including a first external surface having a cylindrical shape, a second external surface having a frustroconical shape, and a plurality of injection holes formed in the distributor that are shaped and adapted to inject ~~and~~ the source element into the reaction chamber in a manner sufficient to allow formation of a thin film is ~~injected through the plurality of injection holes~~; and
a substrate heating member positioned in the reaction chamber.
2. (Original) The apparatus of claim 1, further comprising a ram that is mounted through the bottom portion of the reaction chamber to support the substrate heating member.
3. (Canceled)
4. (Previously presented) The apparatus of claim 1, wherein the plurality of injection holes are arranged on the second external surface of the distributor.
5. (Original) The apparatus of claim 4, wherein each injection hole includes a large diameter part accepting the source element and a small diameter part in which the velocity of source element increases.

6. (Previously Presented) The apparatus of claim 5, wherein the large diameter part has a large diameter rather than the small diameter part.
7. (Original) The apparatus of claim 1, wherein the substrate heating member is positioned at the center of the reaction space and the gas injector is disposed at the center of the top portion of the reaction chamber.
8. (Previously Presented) The apparatus of claim 1, further comprising a plurality of distributors that are classified into a first distributor at the center of the top portion and a second distributor around the first distributor in the top portion so as to inject the source element.
9. (Original) The apparatus of claim 8, wherein the source element includes a primary reactant element and a secondary reactant element.
10. (Original) The apparatus of claim 9, wherein the primary reactant element passes through the first distributor arranged at the center of the top portion and the secondary reactant element passes through the second distributor arranged around the first distributor.
11. (Original) The apparatus of claim 10, wherein an axis of the second distributor forms an angle of about 90 degrees with an axis of the first distributor when the first and second distributors are disposed at the top portion of the reaction chamber.

12. (Original) The apparatus of claim 10, wherein an axis of the second distributor forms an angle of less than 90 degrees with an axis of the first distributor when the first and second distributors are disposed at the top portion of the reaction chamber.
13. (Original) The apparatus of claim 10, wherein the secondary reactant element is selected from a group consisting of ammonia (NH_3), hydrazine (N_2H_4), water vapor (H_2O), oxygen (O_2) and ozone (O_3).
14. (Original) The apparatus of claim 1, wherein the number of and the size of the injection holes vary depending on the reaction space of the reaction chamber.
15. (Original) The apparatus of claim 1, wherein the top portion of the reaction chamber has a dome shape.
16. (Previously Presented) The apparatus of claim 1, wherein the substrate heating member includes a heating element.
17. (Withdrawn) A method for forming a thin film in a deposition apparatus that has a reaction chamber having a reaction space therein, a substrate heating member disposed in the reaction space, a gas injector in a top portion of the reaction chamber, and a distributor connected to the gas injector, the method comprising the steps of:
- streaming a chemical source gas through the gas injector;

injecting the chemical source gas into the reaction space through the distributor that having a plurality of injection holes; and

reacting the chemical source gas, whereby the thin film is formed upon a substrate that is disposed on the substrate heating member.

18. (Withdrawn) The method of claim 17, wherein the distributor includes a first portion having a cylindrical and a second portion shaped like a truncated cone.

19. (Withdrawn) The apparatus of claim 18, wherein the plurality of injection holes are arranged at the side of the second portion of the distributor.

20. (Withdrawn) The apparatus of claim 19, wherein each injection hole includes a large diameter part accepting the chemical source gas and a small diameter part in which the velocity of chemical source gas increases.

21. (Previously Presented) The apparatus of claim 1, wherein the sidewall portion of the reaction chamber includes the substrate inlet/outlet through which a substrate transfers in and out of the reaction chamber, and wherein the bottom portion of the reaction chamber includes a gas exhaust port that emits air from the reaction chamber.

22. (Previously Presented) An apparatus for forming a thin film, comprising:
a reaction chamber having a top portion, a sidewall portion and a bottom portion;
a gas injector penetrating the top portion and letting a source element pass therethrough;

a distributor connected to the gas injector, the distributor comprising a first external portion having a cylindrical shape, a second external portion having a frustroconical shape, and a plurality of injection holes formed in the second portion, each injection hole defining an interface to the reaction chamber, wherein the source element is injected into the reaction chamber through the plurality of injection holes; and

a substrate heating member positioned in the reaction chamber.

23. (New) An apparatus for forming a thin film, comprising:

a reaction chamber having a top portion, a sidewall portion and a bottom portion;

a gas injector penetrating the top portion and letting a source element pass therethrough;

a means forming a thin film on a substrate; and

a substrate heating member positioned in the reaction chamber.

24. (New) The apparatus of claim 23, wherein the means for forming the thin film on the substrate includes means for distributing the source element in the reaction chamber.

25. (New) A method of utilizing the apparatus of claim 23, the method comprising:

positioning a substrate on the substrate heating member, and

forming a thin film on the substrate by injecting a source element through the thin film forming means and into the reaction chamber.

26. (New) A method of utilizing the apparatus of claim 1, the method comprising:
- positioning a substrate on the substrate heating member, and
 - forming a thin film on the substrate by injecting a source element through the thin film distributor and into the reaction chamber.